Comments and Corrections

Corrections to "Device Linearity Comparison of Uniformly Doped and δ-Doped $In_{0.52}Al_{0.48}As/In_{0.6}Ga_{0.4}As$ Metamorphic HEMTs"

Y. C. Lin, Edward Yi Chang, H. Yamaguchi, Y. Hirayama, X. Y. Chang, and C. Y. Chang

In the above paper, [1], Table I was incorrect. The correct table is printed below.

TABLE I
COMPARISON OF THE DC CHARACTERISTICS OF THE UNIFORMLY DOPED AND THE δ-DOPED $In_{0.52}Al_{0.48}As/In_{0.6}Ga_{0.4}As$ MHEMTs

Device Type	δ doped $In_{0.6}Ga_{0.4}As$ MHEMT	Uniformly-doped $In_{0.6}Ga_{0.4}As$ MHEMT
I_{DSS} (I_{DS} @ V_{GS}=0, mA/mm)	414.5	228.0
Gm_{max} (mS/mm)	506.0	401.4
Pinch off voltage:(V)	-1.17	-0.90
a_0	0.06634	0.03627
a_1	0.01835	0.06445
a_2/a_1	-1.555	0.131
a_3/a_1	1.215	-0.359
a_4/a_1	0.403	-0.045
a_5/a_1	-0.472	0.106

REFERENCES

[1] Y. C. Lin, E. Y. Chang, H. Yamaguchi, Y. Hirayama, X. Y. Chang, and C. Y. Chang, "Device linearity comparison of uniformly doped and δ-doped $In_{0.52}Al_{0.48}As/In_{0.6}Ga_{0.4}As$ metamorphic HEMTs," *IEEE Electron Device Lett.*, vol. 27, no. 7, pp. 535–537, Jul. 2006.

Manuscript received February 14, 2006; revised March 29, 2006. This work was supported by the Ministry of Education, the Ministry of Economic Affairs, and the National Science Council of the Republic of China under Contracts NSC 94-2752-E-009-001-PAE and 94-EC-17-A-05-S1-020. The review of this letter was arranged by Editor J. del Alamo.

Y. C. Lin, E. Y. Chang, and X. Y. Chang are with the Department of Materials Science and Engineering and Microelectronics and Information Systems Research Center, National Chiao Tung University, Hsinchu 30010, Taiwan, R.O.C. (e-mail: edc@mail.nctu.edu.tw).

H. Yamaguchi and Y. Hirayama are with NTT Basic Research Laboratories, Atsugi 243-0198, Japan.

C. Y. Chang is with the Department of Electronics Engineering, National Chiao Tung University, Hsinchu 30010, Taiwan, R.O.C.

Digital Object Identifier 10.1109/LED.2006.877307

Digital Object Identifier 10.1109/LED.2006.884081